



N-Channel 80 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) (Max.)	I _D (A) ^{a, g}	Q _g (Typ.)
80	0.0062 at V _{GS} = 10 V	60	24 nC
	0.0065 at V _{GS} = 7.5 V		
	0.0095 at V _{GS} = 4.5 V		

FEATURES

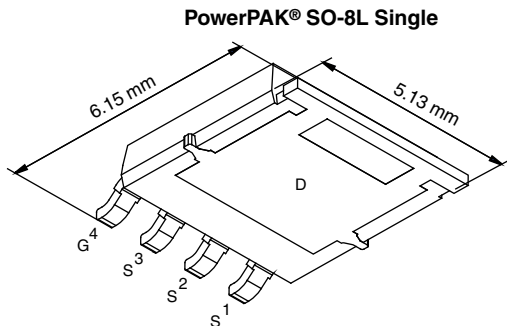
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- Capable of Operating with 5 V Gate Drive
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



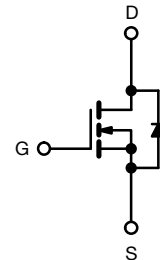
RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- DC/DC Primary Side Switch
- Synchronous Rectification
- High Current Switching



Ordering Information:
SiJ482DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	80	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	60 ^g
		T _C = 70 °C	60 ^g
		T _A = 25 °C	21.1 ^{b, c}
		T _A = 70 °C	16.9 ^{b, c}
Pulsed Drain Current (t = 300 μs)	I _{DM}	100	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	4.5 ^{b, c}
Single Pulse Avalanche Current	I _{AS}	30	mJ
Single Pulse Avalanche Energy	E _{AS}	45	
Maximum Power Dissipation	P _D	T _C = 25 °C	69.4
		T _C = 70 °C	44.4
		T _A = 25 °C	5 ^{b, c}
		T _A = 70 °C	3.2 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	20	25	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	1.3	1.8	

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 65 °C/W.
- Package limited.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	80			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		36		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.7			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.5		2.7	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V			1	μA	
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 55 °C			10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30			A	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0051	0.0062	Ω	
		V _{GS} = 7.5 V, I _D = 15 A		0.0054	0.0065		
		V _{GS} = 4.5 V, I _D = 10 A		0.0068	0.0095		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 20 A		68		S	
Dynamic^b							
Input Capacitance	C _{iss}	V _{DS} = 40 V, V _{GS} = 0 V, f = 1 MHz		2425		pF	
Output Capacitance	C _{oss}			1180			
Reverse Transfer Capacitance	C _{rss}			100			
Total Gate Charge	Q _g	V _{DS} = 40 V, V _{GS} = 10 V, I _D = 10 A		47	71	nC	
		V _{DS} = 40 V, V _{GS} = 7.5 V, I _D = 10 A		36.5	55		
Gate-Source Charge	Q _{gs}	V _{DS} = 40 V, V _{GS} = 4.5 V, I _D = 10 A		24	36		
				6.6			
Gate-Drain Charge	Q _{gd}			10.2			
Output Charge	Q _{oss}		V _{DS} = 40 V, V _{GS} = 0 V		69		105
Gate Resistance	R _g		f = 1 MHz	0.4	1.1	2.2	Ω
Turn-On Delay Time	t _{d(on)}		V _{DD} = 40 V, R _L = 4 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		14	28	ns
Rise Time	t _r			11	22		
Turn-Off Delay Time	t _{d(off)}			36	72		
Fall Time	t _f			9	18		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 40 V, R _L = 4 Ω I _D ≅ 10 A, V _{GEN} = 7.5 V, R _g = 1 Ω		16	32		
Rise Time	t _r			13	26		
Turn-Off Delay Time	t _{d(off)}			35	70		
Fall Time	t _f			11	22		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			60	A	
Pulse Diode Forward Current ^a	I _{SM}				100		
Body Diode Voltage	V _{SD}	I _S = 4 A		0.73	1.1	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C		46	90	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			44	86	nC	
Reverse Recovery Fall Time	t _a			21		ns	
Reverse Recovery Rise Time	t _b			25			

Notes:

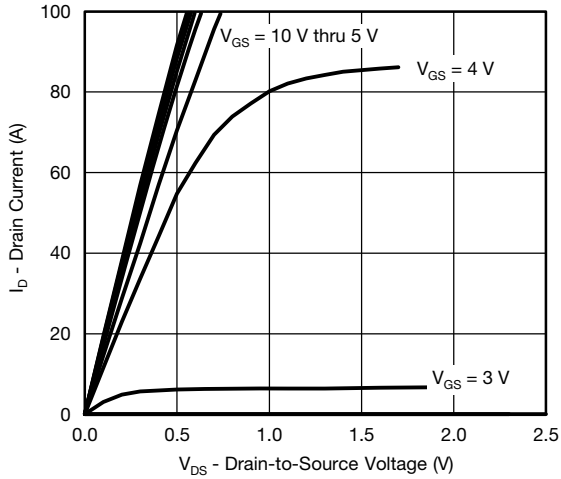
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.

b. Guaranteed by design, not subject to production testing.

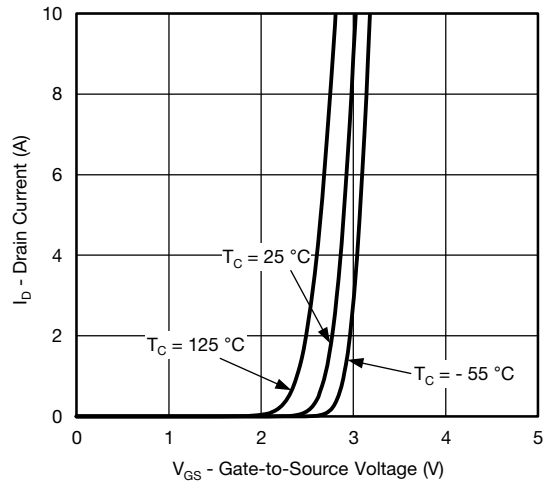
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



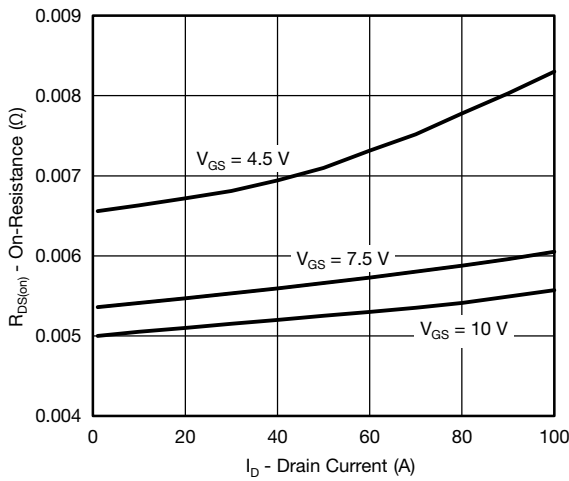
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



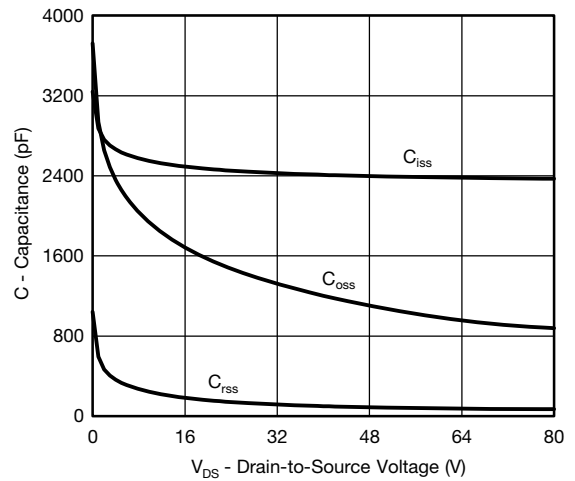
Output Characteristics



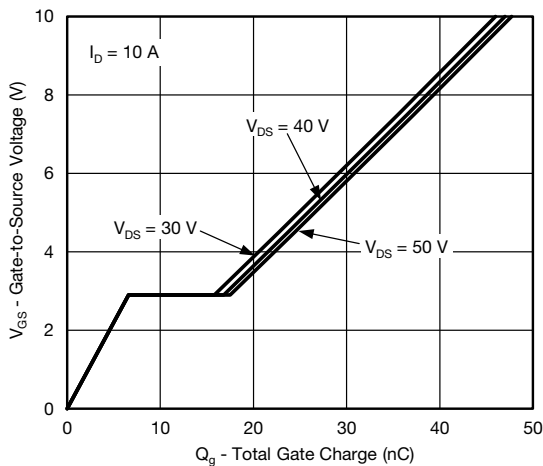
Transfer Characteristics



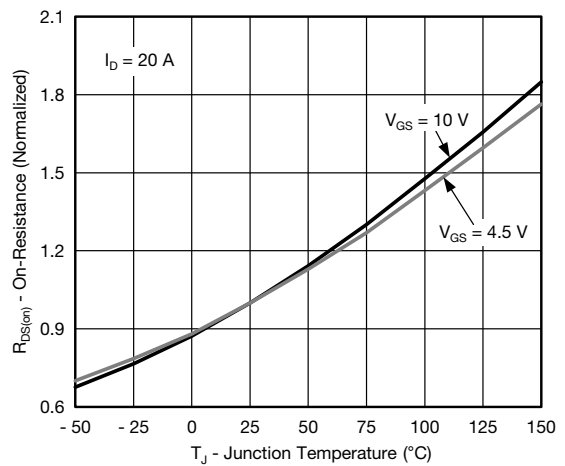
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



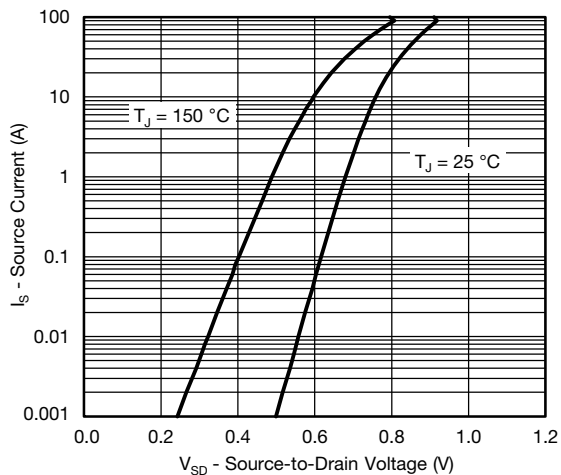
Gate Charge



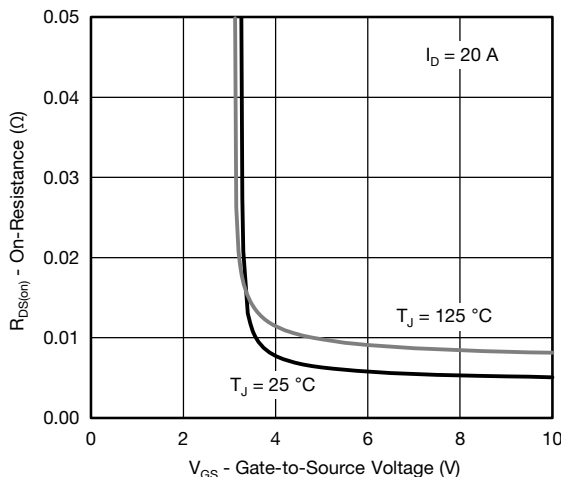
On-Resistance vs. Junction Temperature



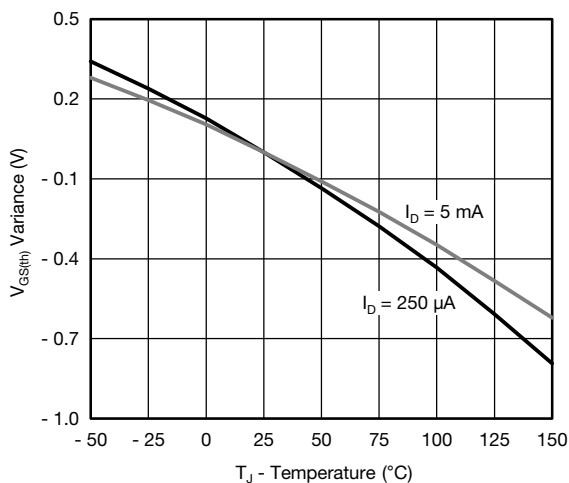
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



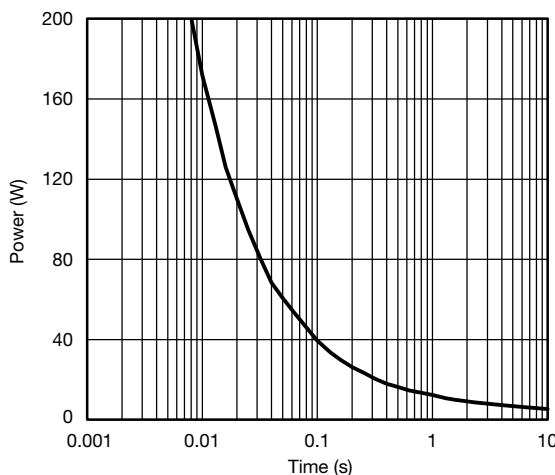
Source-Drain Diode Forward Voltage



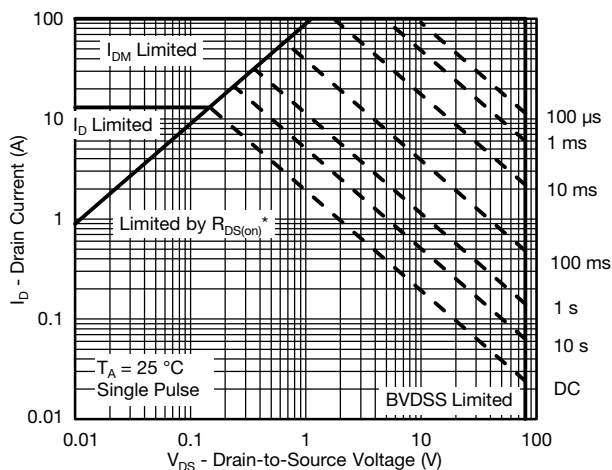
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



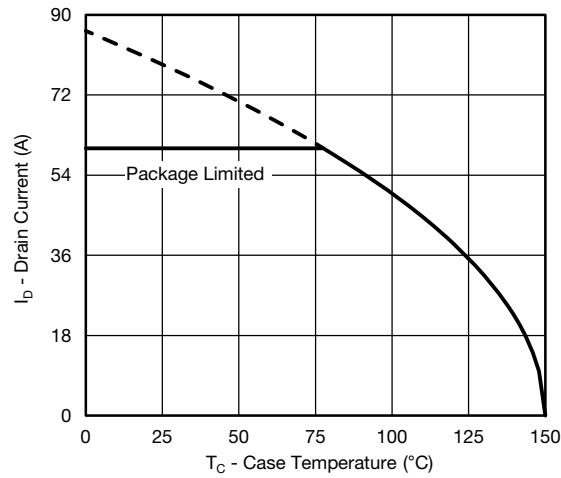
Single Pulse Power, Junction-to-Ambient



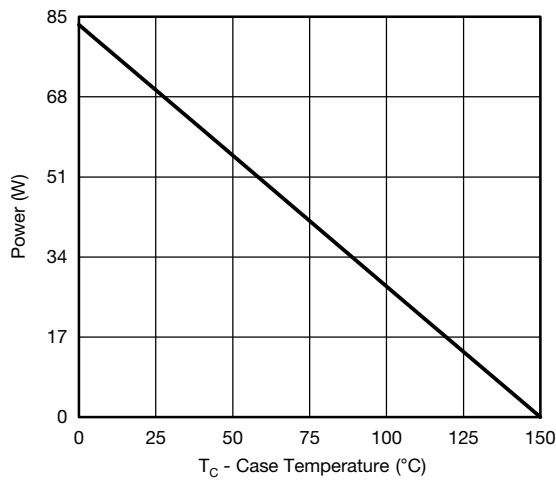
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient



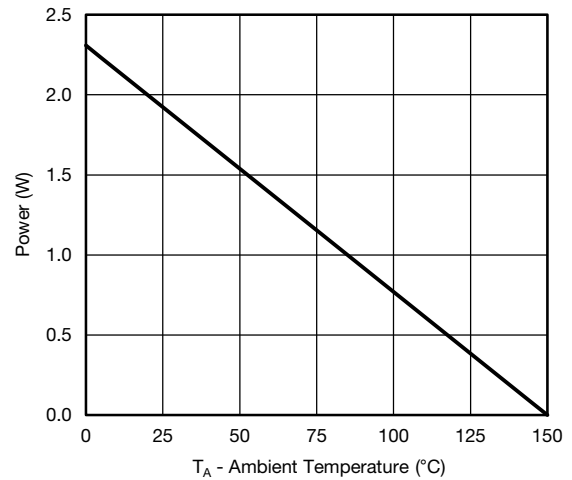
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



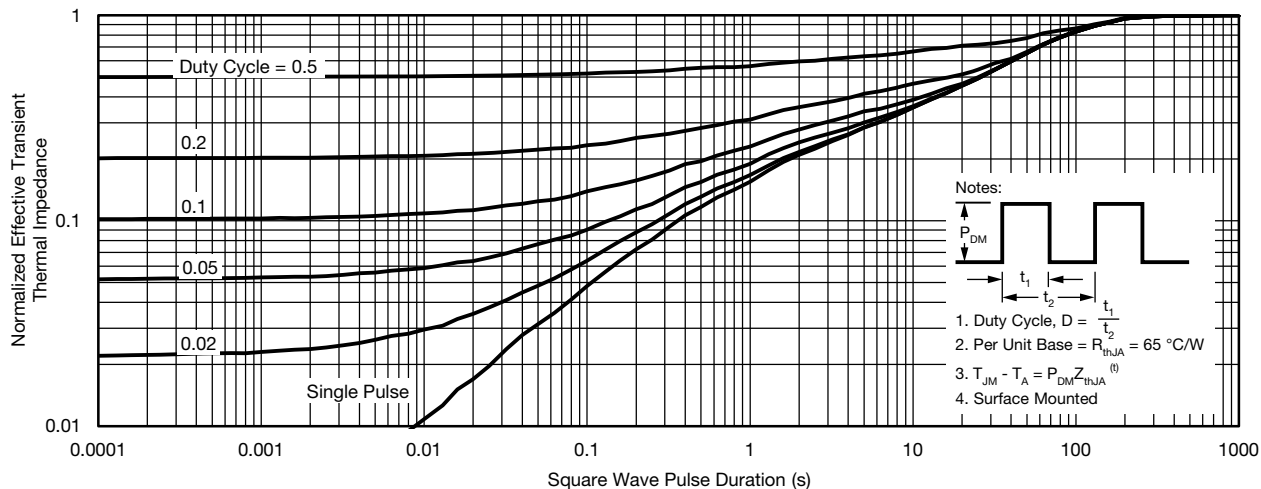
Power, Junction-to-Case



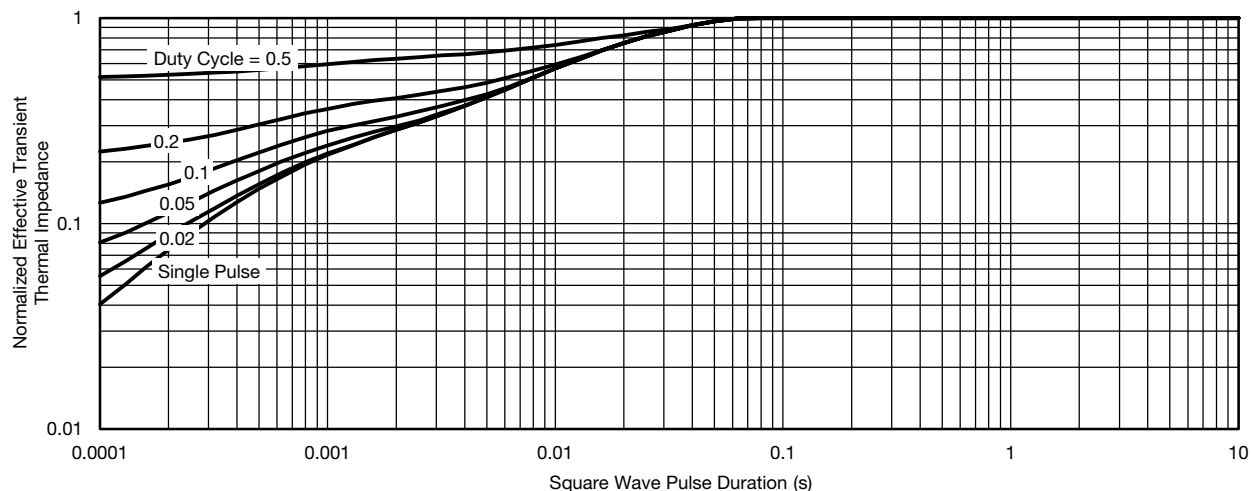
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

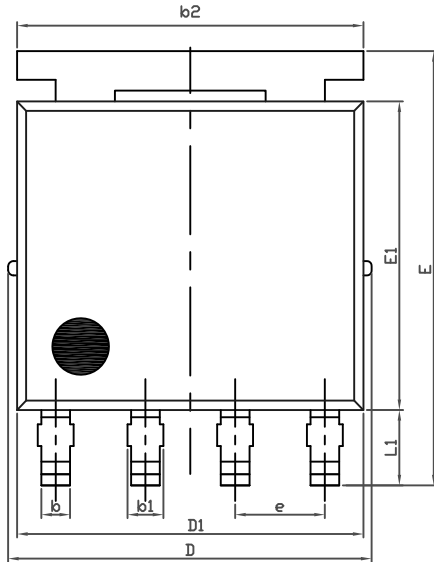


Normalized Thermal Transient Impedance, Junction-to-Case

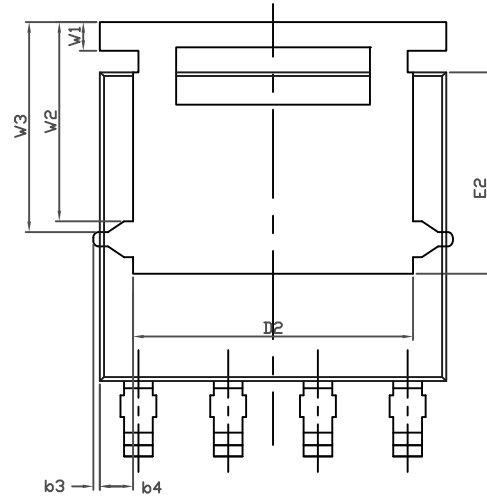
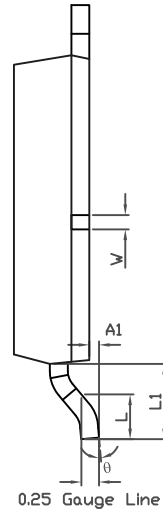
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63728.



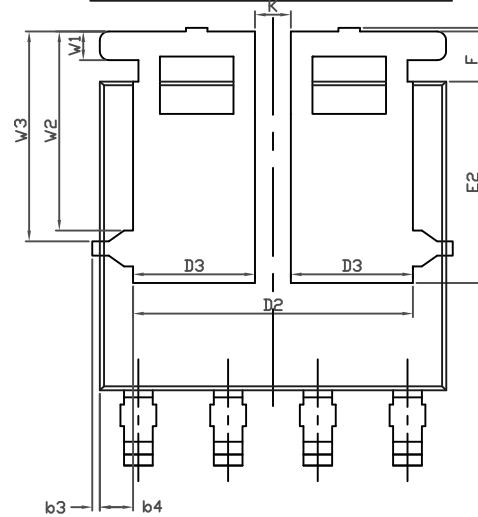
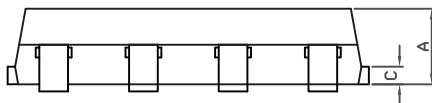
PowerPAK[®] SO-8L Case Outline for Non-AI Parts



TOPSIDE VIEW



BACKSIDE VIEW(SINGLE)



BACKSIDE VIEW(DUAL)



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.094			0.004		
b4	0.47			0.019		
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51			0.020		
W	0.23			0.009		
W1	0.41			0.016		
W2	2.82			0.111		
W3	2.96			0.117		
q	0°	-	10°	0°	-	10°
ECN: C15-1122-Rev. C, 07-Sep-15 DWG: 5976						

Note

- Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads
Dimensions in mm (inches)



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